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November 2006

FDFS2P753Z

Integrated P-Channel PowerTrench® MOSFET and Schottky Diode

-30V, -3A, 115mΩ

Features

- Max $r_{DS(on)}$ = 115m Ω at V_{GS} = -10V, I_D = -3.0A
- Max $r_{DS(on)}$ = 180m Ω at V_{GS} = -4.5V, I_D = -1.5A
- V_F < 500mV @ 1A

V_F < 580mV @ 2A

- Schottky and MOSFET incorporated into single power surface mount SO-8 package
- Electrically independent Schottky and MOSFET pinout for design flexibility
- RoHS Compliant



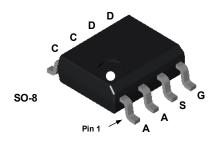
General Description

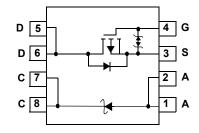
The FDFS2P753Z combines the exceptional performance of Fairchild's PowerTrench MOSFET technology with a very low forward voltage drop Schottky barrier rectifier in an SO-8 package.

This device is designed specifically as a single package solution for DC to DC converters. It features a fast switching, low gate charge MOSFET with very low on-state resistance. The independently connected Schottky diode allows its use in a variety of DC/DC converter topologies.

Application

■ DC - DC Conversion





MOSFET Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		-30	V
V_{GS}	Gate to Source Voltage		±25	V
	Drain Current -Continuous	(Note 1a)	-3	А
ID	-Pulsed		-16	^
P_{D}	Power Dissipation	(Note 1a)	1.6	W
E _{AS}	Single Pulse Avalanche Energy (Note 2)		6	mJ
V_{RRM}	Schottky Repetitive Peak Reverse Voltage		-20	V
Io	Schottky Average Forward Current	(Note 1a)	-2	Α
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	Ô

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	40	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDFS2P753Z	FDFS2P753Z	SO-8	330mm	12mm	2500 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25°C		-21		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24V,$ $V_{GS} = 0V$ $T_{J} = 125^{\circ}C$			-1 -100	μА
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±25V, V _{DS} = 0V			±10	μА

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250 \mu A$	-1	-2.1	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25°C		5		mV/°C
	$V_{GS} = -10V, I_D = -3.0A$		69	115		
r _{DO(})	Drain to Source On-Resistance	$V_{GS} = -4.5V$, $I_{D} = -1.5A$		115	180	mΩ
r _{DS(on)} Drain to	Diam to obtaine on registance	$V_{GS} = -10V$, $I_D = -3.0A$, $T_J = 125$ °C		97	162	11132
g _{FS}	Forward Transconductance	$V_{DS} = -5V, I_{D} = -3.0A$		6		S

Dynamic Characteristics

C _{iss}	Input Capacitance	\\ - 40\\ \\ - 0\\	340	455	pF
Coss	Output Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz	80	110	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1101112	65	100	pF
R_g	Gate Resistance	f = 1MHz	18		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	.,	7	14	ns
t _r	Rise Time	$V_{DD} = -10V, I_{D} = -3.0A$ $V_{GS} = -10V, R_{GEN} = 6\Omega$	31	50	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = -10V, R _{GEN} = 002	18	33	ns
t _f	Fall Time		20	35	ns
$Q_{g(TOT)}$	Total Gate Charge at -10V	V _{GS} = 0V to -10V	6.6	9.3	nC
Q _{g(4.5)}	Total Gate Charge at -4.5V	$V_{GS} = 0V \text{ to } -4.5V$ $V_{DD} = -10V$ $I_{D} = -3.0A$	3.3	4.6	nC
Q_{gs}	Gate to Source Gate Charge	I _D = -3.0A	1.3		nC
Q _{gd}	Gate to Drain "Miller" Charge		1.6		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = -2.0A$ (Note 3)		-0.9	-1.2	V
t _{rr}	Reverse Recovery Time	I _F = -3.0A, di/dt = 100A/μs		20	30	ns
Q_{rr}	Reverse Recovery Charge			14	21	nC

Schottky Diode Characteristics

I _R F	Povorso Logicado	\/_ = 20\/	T _J = 25°C	-190	μА
	Reverse Leakage	O O	T _J = 125°C	-66	mA
V _F Forward V		I _E = 1A	T _J = 25°C	0.5	V
	Forward Voltage	IF - IA	T _J = 125°C	0.39	
	Forward Voltage	I - 24	T _J = 25°C	0.58	
		I _F = 2A	T _J = 125°C	0.53	

Notes:

 R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0CA} is determined by the user's board design.



a) 78°C/W when mounted on a 0.5in2 pad of 2 oz copper



b) 135°C/W when mounted on a minimun pad

2: Starting T $_J$ = 25°C, L = 3mH, I $_{AS}$ = 2A, V $_{DD}$ = 27V, V $_{GS}$ = 10V 3: Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

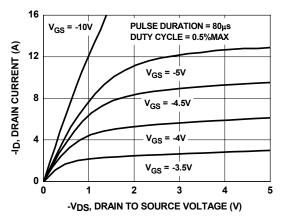


Figure 1. On Region Characteristics

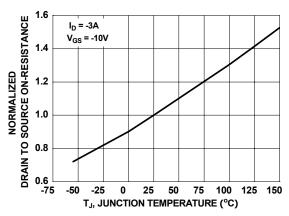


Figure 3. Normalized On-Resistance vs Junction Temperature

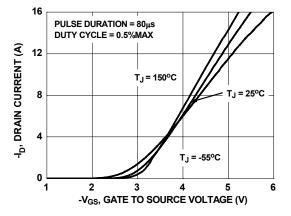


Figure 5. Transfer Characteristics

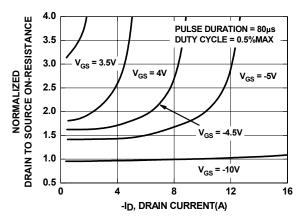


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

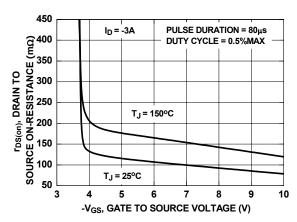


Figure 4. On-Resistance vs Gate to Source Voltage

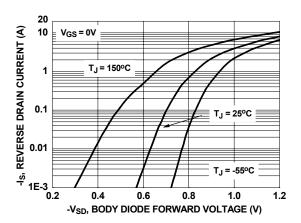


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

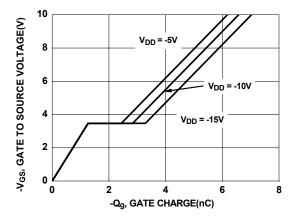


Figure 7. Gate Charge Characteristics

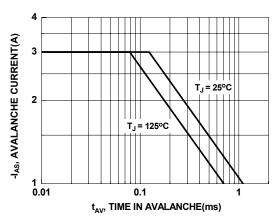


Figure 9. Unclamped Inductive Switching Capability

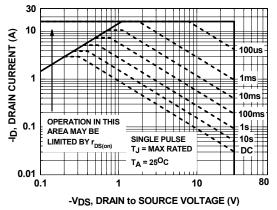


Figure 11. Forward Bias Safe Operating Area

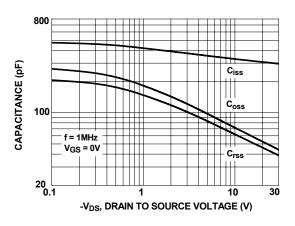


Figure 8. Capacitance vs Drain to Source Voltage

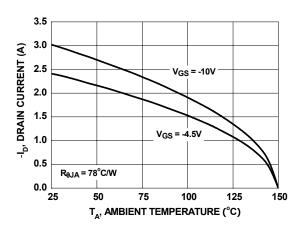


Figure 10. Maximum Continuous Drain Current vs Case Temperature

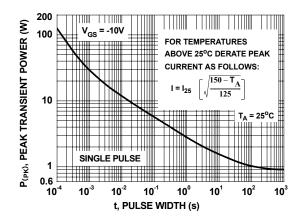
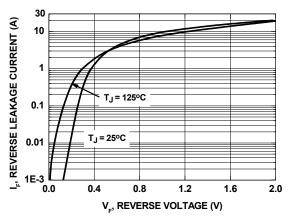


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted



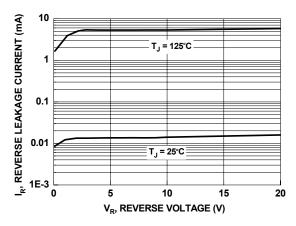


Figure 13. Schottky Diode Forward Voltage

Figure 14. Schottky Diode Reverse Current

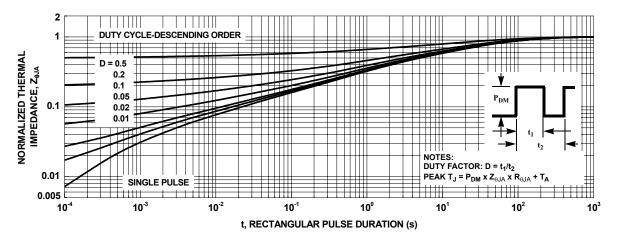


Figure 15. Transient Thermal Response Curve





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Deminition of Terms		
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